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temperature of the reacting chamber ambient is stabilizing within a first temperature range;

forming a second [HSG] hemispherical grain (HSG) nuclei over the first HSG nuclei by introducing a second amount of the source gas into the reacting chamber after the [ambient] temperature of the reacting chamber ambient stabilizes within the first temperature range to form a resulting structure; and annealing the resulting structure.

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B2      – Claim 5. (Amended) The method according to claim 1, wherein the resulting structure is formed on a conductive layer pattern on a substrate and the [ambient] temperature of the reacting chamber ambient is stabilized at the first temperature range by heating the substrate at a temperature between 500 °C and 630 °C. –

– Claim 6. (Amended) the method according to claim 1, wherein [the] said first temperature range [of the ambient temperature] is between 200 °C and 500 °C. –

-- Claim 7. ( Twice Amended) A method for depositing a hemispherical grain layer over a conductive layer pattern of a capacitor electrode on a substrate in [an] a reacting chamber ambient for forming a semiconductor capacitor, the method comprising:

introducing a first amount of a source gas into the reacting chamber ambient, while heating the reacting chamber ambient, to form a first plurality of hemispherical sections while a temperature of the substrate is stabilizing within

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a first temperature range;

introducing a second amount of the source gas into the reacting chamber ambient to form a second plurality of hemispherical sections over the first plurality of hemispherical sections after the temperature of the substrate stabilizes within the first temperature range to form a resulting structure; and annealing the resulting structure. --

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B3

-- Claim 11. (Amended) The method according to claim 7, wherein an internal pressure of the reacting chamber ambient is less than  $1 \times 10^{-3}$  torr. --

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B4

-- Claim 13. (Amended) The method according to claim 7, wherein heat radiating from the substrate stabilizes the reacting chamber ambient while a temperature of the of the substrate stabilizes within a first temperature range. --

-- Claim 14. (Twice Amended) A method for forming a capacitor electrode of a capacitor in a reacting chamber, the method comprising:

forming a first [HSG] hemispherical grain (HSG) nuclei by introducing a first source gas into the reacting chamber during a period while [an ambient] the temperature of the reacting chamber ambient is stabilizing at a first temperature range;

forming a second [HSG] hemispherical grain (HSG) nuclei over the first HSG nuclei by introducing a second source gas into the reacting chamber after the temperature of the reacting chamber ambient temperature stabilizes at the first temperature range to form a resulting structure; and annealing the resulting structure. --

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BS -- Claim 16. (Amended) The method according to claim 7, further comprising pre-heating the first amount of source gas to about 35°C prior to introducing the first amount of source gas into the reacting chamber ambient.--

-- Claim 17. (Amended) The method according to claim 16, wherein the reacting chamber ambient is heated to a temperature between 200°C and 500°C.--

### Remarks

The Office Action of February 10, 2000 has been carefully studied and reviewed, and in view of the foregoing amendment and following representations, reconsideration is respectfully requested.

#### I. Claim Objections

Applicants' have amended the claims in the manner suggested by the Examiner, although reasons for such objections were not stated in the Office Action and such reasons for the objections remain unclear to Applicants. The only exception to Applicants' compliance with the Examiner's requirements to amend the claims is claim 4; claim 4 includes none of those phrases identified by the Examiner in the Office Action as being objectionable.

It is further noted that Applicants did not make such amendments earlier because the Examiner has only raised the aforementioned objections in the last Office Action. It is thus respectfully requested that the amendments be entered as not affecting the scope of the claims, and that the objection to the claims be withdrawn.